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Complete if Known Substitute for form 1449/PTO **Application Number** 10/799325 Filing Date Mar 12, 2004 INFORMATION DISCLOSURE First Named Inventor Randy Hoffman STATEMENT BY APPLICANT Art Unit 2811 (Use as many sheets as necessary) **Examiner Name** Thien Tran Attorney Docket Number 200315134-1 Sheet 1 of 2

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STATEMENT BY APPLICANT	First Named Inventor	Randy Hoffman
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